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NXP Semiconductors/Freescale Semiconductor, Inc. PMPB15XP,115

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Distributor of NXP Semiconductors/Freescale Semiconductor, Inc. : Excellent Integrated Datasheet of PMPB15XP,115 - MOSFET P-CH 12V 8.2A 6DFN Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

PMPB15XP

12 V, single P-channel Trench MOSFET 19 July 2012

Product data sheet

1. Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 1.5 kV ESD protection (human body model)
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- · Power management in battery-driven portable devices
- Hard disk and computing power management

1.4 Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-12	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-11.8	А
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I _D = -8.2 A; T _j = 25 °C		-	15	19	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².







PMPB15XP

12 V, single P-channel Trench MOSFET

Pinning information 2.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		D
2	D	drain		
3	G	gate		G
4	S	source		\$ 017aaa257
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

Ordering information 3.

Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PMPB15XP	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220				

Marking 4.

Table 4. Marking codes	
Type number	Marking code
PMPB15XP	1A

Limiting values 5.

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-12	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-11.8	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-8.2	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-5.2	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-33	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
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PMPB15XP

12 V, single P-channel Trench MOSFET

Symbol	Parameter	Conditions		Min	Max	Unit
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					_
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.9	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

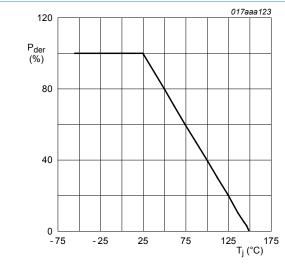


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

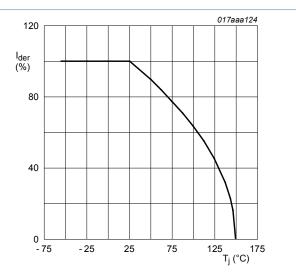


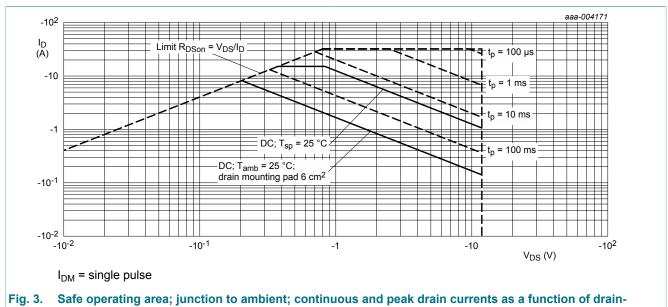
Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$



PMPB15XP





source voltage

6. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	235	270	K/W
			[2]	-	67	74	K/W
		in free air; t ≤ 5 s	[2]	-	33	36	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

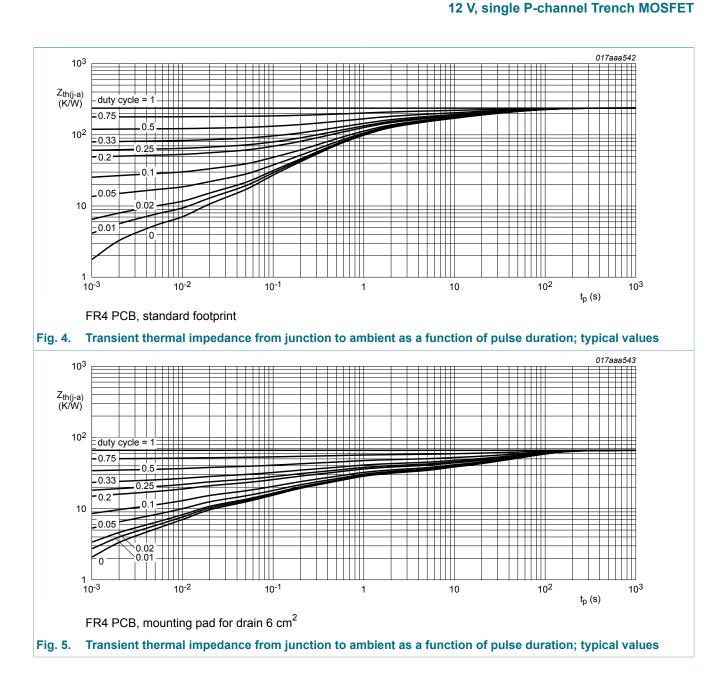
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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7. Characteristics

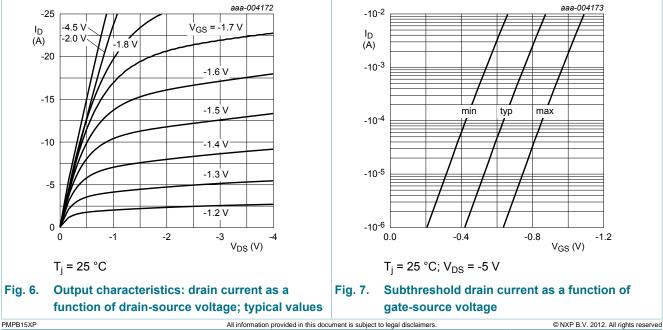
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics	· · ·				
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C	-12	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.47	-0.68	-0.9	V
I _{DSS}	drain leakage current	V_{DS} = -12 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{DS} = -12 V; V _{GS} = 0 V; T _j = 150 °C	-	-	-100	μA



PMPB15XP

12 V, single P-channel Trench MOSFET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
		V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I _D = -8.2 A; T _j = 25 °C	-	15	19	mΩ
	resistance	V_{GS} = -4.5 V; I _D = -8.2 A; T _j = 150 °C	-	20	25	mΩ
		V_{GS} = -2.5 V; I _D = -3.9 A; T _j = 25 °C	-	17	20	mΩ
		V_{GS} = -1.8 V; I _D = -3.9 A; T _j = 25 °C	-	21	30	mΩ
9 _{fs}	forward transconductance	V _{DS} = -10 V; I _D = -8.2 A; T _j = 25 °C	-	40	-	S
Dynamic cl	haracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = -6 V; I _D = -8.2 A; V _{GS} = -4.5 V; T _j = 25 °C	-	67	100	nC
Q _{GS}	gate-source charge		-	5.5	-	nC
Q _{GD}	gate-drain charge		-	7.3	-	nC
C _{iss}	input capacitance	V_{DS} = -6 V; f = 1 MHz; V_{GS} = 0 V;	-	2875	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	570	-	pF
C _{rss}	reverse transfer capacitance	-	-	530	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -6 V; I _D = -8.2 A; V _{GS} = -4.5 V;	-	18	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	90	-	ns
t _{d(off)}	turn-off delay time		-	85	-	ns
t _f	fall time		-	57	-	ns
Source-dra	in diode	,	I I			
V _{SD}	source-drain voltage	I _S = -1.9 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.6	-1.2	V



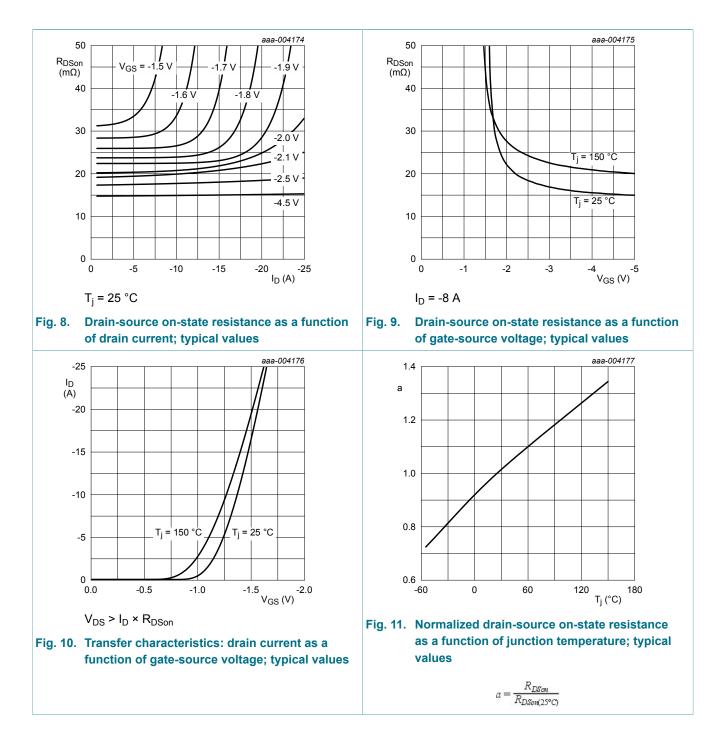


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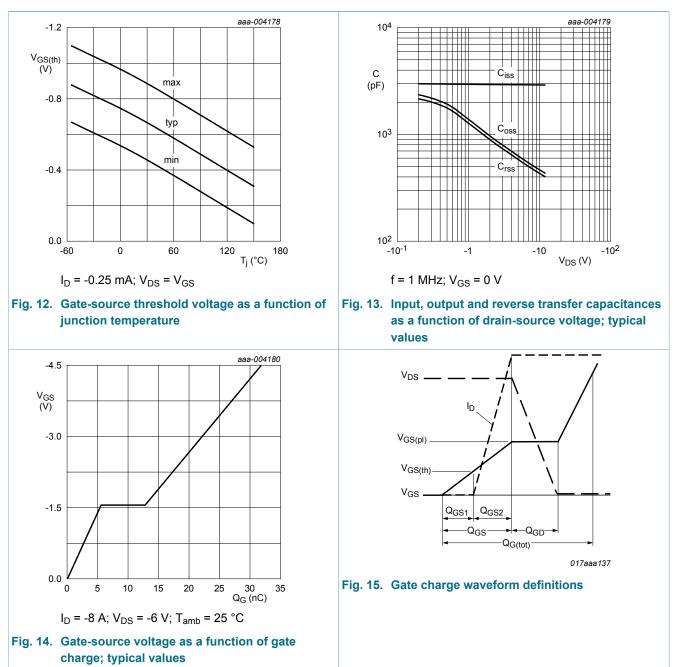


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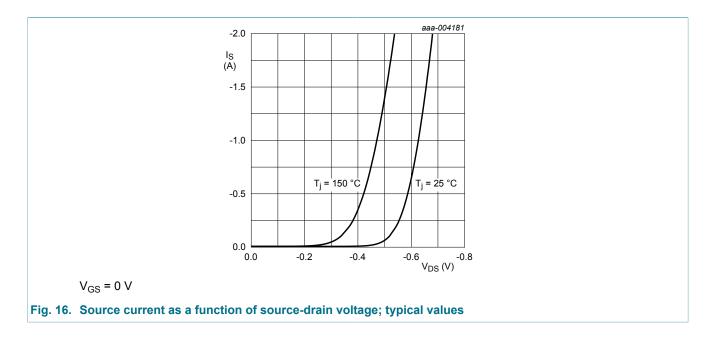




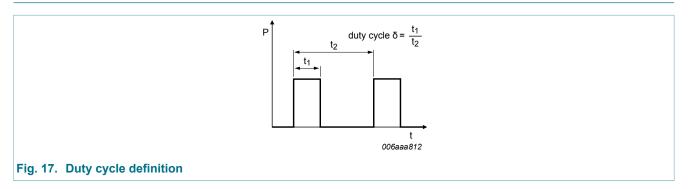


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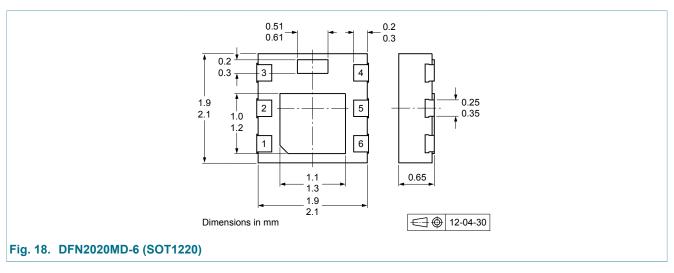
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Test information 8.



Package outline 9.



Product data sheet

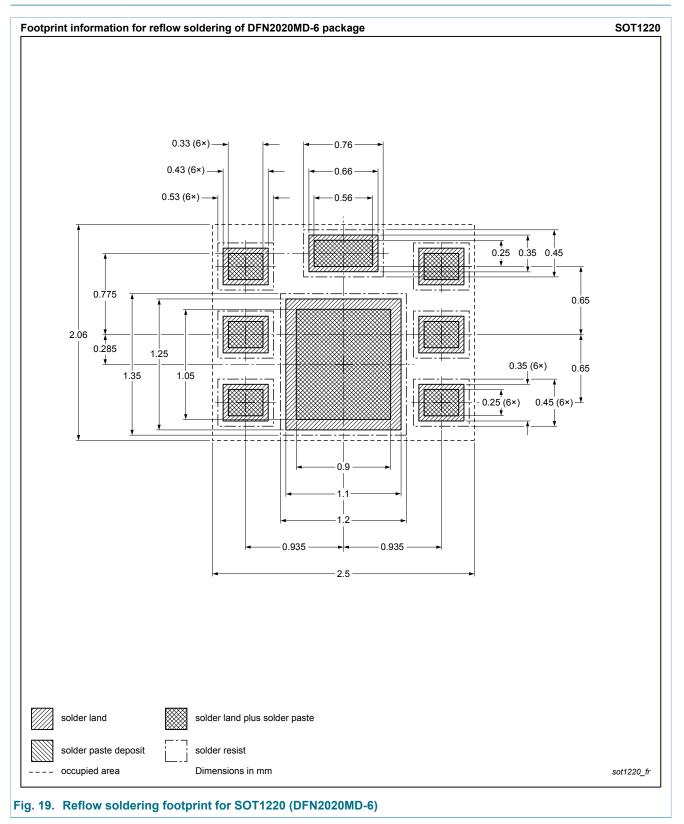
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12 V, single P-channel Trench MOSFET

10. Soldering



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12 V, single P-channel Trench MOSFET

11. Revision history

Table 8. Revision history								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMPB15XP v.2	20120719	Product data sheet	-	PMPB15XP v.1				
Modifications:		Section 1 "Product profile": V_{ESD} updated Table 7 "Characteristics": C_{iss} , C_{oss} and C_{rss} updated						
PMPB15XP v.1	20120706	Preliminary data sheet	-	-				



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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PMPB15XP

12 V, single P-channel Trench MOSFET

13. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	4
7	Characteristics	5
8	Test information	9
9	Package outline	9
10	Soldering	10
11	Revision history	11
12	Legal information	12
12.1	Data sheet status	12
12.2	Definitions	12
12.3	Disclaimers	12
12.4	Trademarks	13

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